

**isc Silicon PNP Power Transistor**
**2SA1075**
**DESCRIPTION**

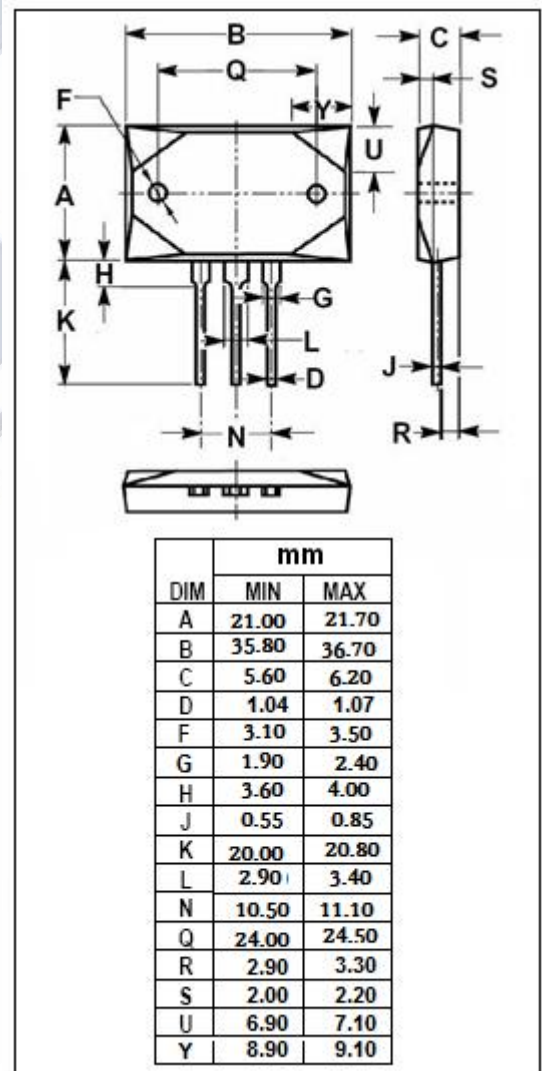
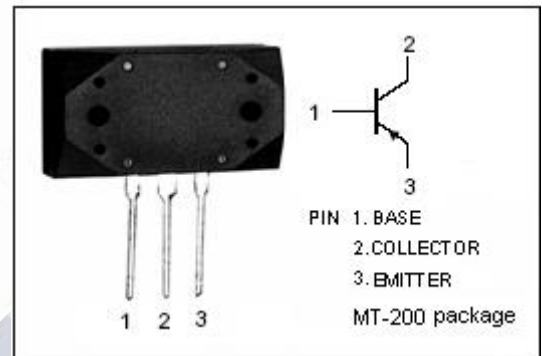
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -160V(\text{Min})$
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC2525
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Power amplifier applications
- switching regulators
- DC-DC converter applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-7	V
$I_C$	Collector Current-Continuous	-12	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	120	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$



**isc Silicon PNP Power Transistor****2SA1075****ELECTRICAL CHARACTERISTICS**T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter –Base Breakdown Voltage	I <sub>C</sub> =- 50μA ; I <sub>B</sub> = 0	-7			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =- 1mA ; I <sub>B</sub> = 0	-120			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =- 50μA ; I <sub>B</sub> = 0	-120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A		-0.9	-1.8	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0			-50	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = -120V; R <sub>EB</sub> =∞			-1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -7V; I <sub>C</sub> =0			-50	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> =-1A; V <sub>CE</sub> = -5V	60		200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = - 7A; V <sub>CE</sub> = -5V	40			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		300	470	pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -1A; V <sub>CE</sub> = -10V, f=10MHZ	45	60		MHz

## Switching times

t <sub>on</sub>	Turn-on Time			0.15		μ s
t <sub>stg</sub>	Storage Time	I <sub>C</sub> =- 7.5A , R <sub>L</sub> = 4 Ω , I <sub>B1</sub> = -I <sub>B2</sub> = -0.75A		0.5		μ s
t <sub>f</sub>	Fall Time			0.11		μ s

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